Elektronische Bauelemente

SS8550T

PNP Silicon
General Purpose Transistor

RoHS Compliant Product

A suffix of "-C" specifies halogen & lead-free

FEATURES

Power dissipation

P_{CM} : 1 W

Collector Current

I_{CM} : -1.5 A

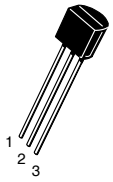
Collector-base voltage

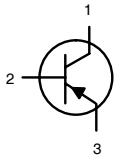
$V_{(BR)CBO}$: - 40 V

Operating & storage junction temperature

T_j, T_{stg} : - 55°C ~ + 150° C

TO-92





1. EMITTER
2. BASS
3. COLLECTOR

ELECTRICAL CHARACTERISTICS (Tamp.=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	Ic= -100 μ A, I_E=0	-40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	Ic= -0.1mA, I_B=0	-25			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=-100 μ A, I_C=0	-5			V
Collector cut-off current	I_{CBO}	V_{CB}=-40 V , I_E=0			-0.1	μ A
Collector cut-off current	I_{CEO}	V_{CE}=-20V , I_B=0			-0.1	μ A
Emitter cut-off current	I_{EBO}	V_{EB}= -5V , I_C=0			-0.1	μ A
DC current gain	$H_{FE(1)}$	V_{CE}=-1V, I_C= -100mA	85		400	
	$H_{FE(2)}$	V_{CE}=-1V, I_C= -800mA	40			
Collector-emitter saturation voltage	V_{CE}(sat)	I_C=-800 mA, I_B=-80mA			-0.5	V
Base-emitter saturation voltage	V_{BE}(sat)	I_C=-800 mA, I_B=-80mA			-1.2	V
Transition frequency	f_T	V_{CE}=-10V, I_C= -50mA f=30MHz	100			MHz

CLASSIFICATION OF $h_{FE(1)}$

Rank	B	C	D	E
Range	85-160	120-200	160-300	300-400

Typical Characteristics

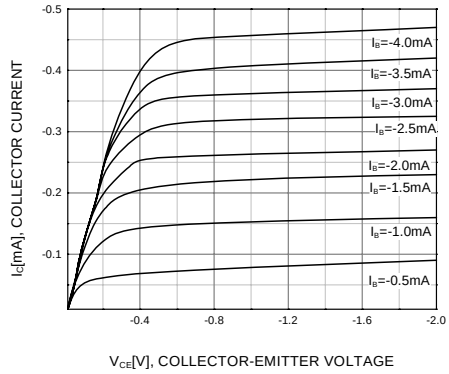


Figure 1. Static Characteristic

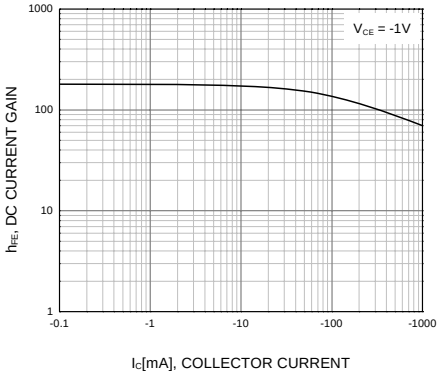


Figure 2. DC current Gain

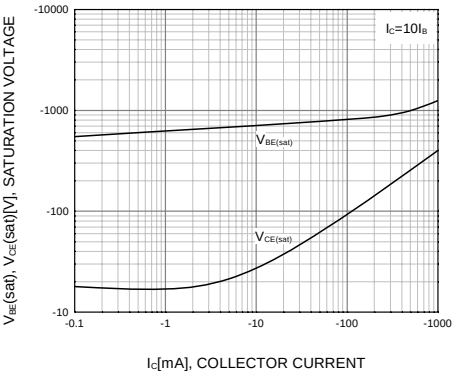


Figure 3. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

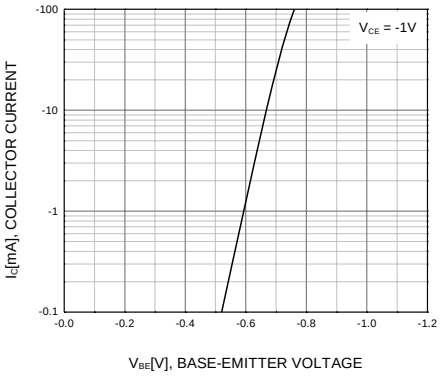


Figure 4. Base-Emitter On Voltage

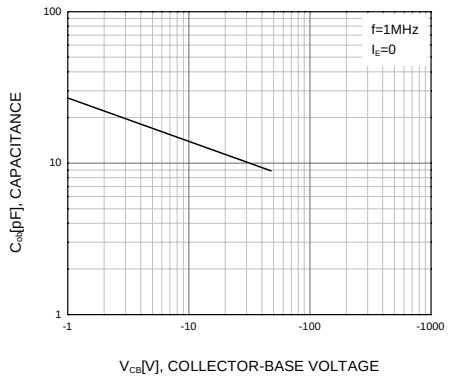


Figure 5. Collector Output Capacitance

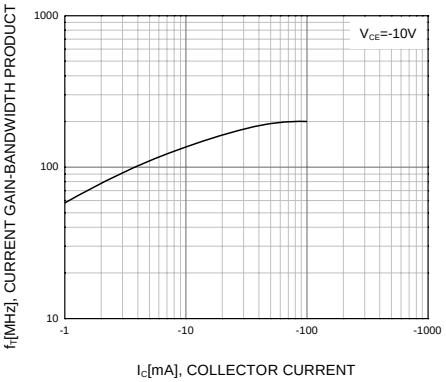


Figure 6. Current Gain Bandwidth Product